

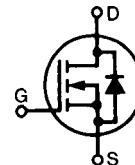
HiPerFET™ Power MOSFETs Q-Class

IXFH 66N20Q
IXFT 66N20Q

V_{DSS} = 200 V
I_{D25} = 66 A
R_{DS(on)} = 40 mΩ

t_{rr} ≤ 200 ns

N-Channel Enhancement Mode
Avalanche Rated High dv/dt, Low Q_g

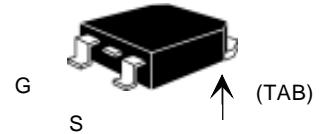


Preliminary data sheet

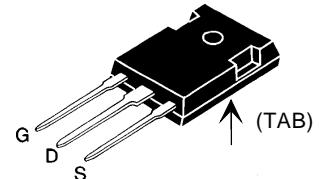
Symbol	Test Conditions	Maximum Ratings		
V _{DSS}	T _J = 25°C to 150°C	200	V	
V _{DGR}	T _J = 25°C to 150°C; R _{GS} = 1 MΩ	200	V	
V _{GS}	Continuous	±30	V	
V _{GSM}	Transient	±40	V	
I _{D25}	T _C = 25°C	66	A	
I _{DM}	T _C = 25°C, pulse width limited by T _{JM}	264	A	
I _{AR}	T _C = 25°C	66	A	
E _{AR}	T _C = 25°C	40	mJ	
E _{AS}	T _C = 25°C	1.5	J	
dv/dt	I _S ≤ I _{DM} , di/dt ≤ 100 A/μs, V _{DD} ≤ V _{DSS} , T _J ≤ 150°C, R _G = 2 Ω	20	V/ns	
P _D	T _C = 25°C	400	W	
T _J		-55 ... +150	°C	
T _{JM}		150	°C	
T _{stg}		-55 ... +150	°C	
T _L	1.6 mm (0.062 in.) from case for 10 s	300	°C	
M _d	Mounting torque	1.13/10	Nm/lb.in.	
Weight	TO-247	6	g	
	TO-268	4	g	

Symbol	Test Conditions (T _J = 25°C, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
V _{DSS}	V _{GS} = 0 V, I _D = 250 μA	200		V
V _{GS(th)}	V _{DS} = V _{GS} , I _D = 4 mA	2.0		V
I _{GSS}	V _{GS} = ±30 V _{DC} , V _{DS} = 0		±100	nA
I _{DSS}	V _{DS} = V _{DSS} V _{GS} = 0 V	T _J = 25°C T _J = 125°C	25 1	μA mA
R _{DS(on)}	V _{GS} = 10 V, I _D = 0.5 I _{D25} Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %		40	mΩ

TO-268 (D3) (IXFT) Case Style



TO-247 AD



G = Gate D = Drain
S = Source TAB = Drain

Features

- IXYS advanced low Q_g process
- International standard packages
- Low gate charge and capacitance
 - easier to drive
 - faster switching
- Low R_{DS(on)}
- Unclamped Inductive Switching (UIS) rated
- Molding epoxies meet UL 94 V-0 flammability classification

Advantages

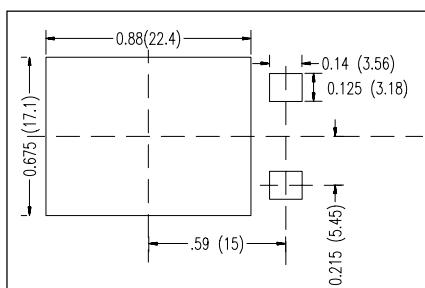
- Easy to mount
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values			
		(T _J = 25°C, unless otherwise specified)	Min.	Typ.	Max.
g_{fs}	V _{DS} = 10 V; I _D = 0.5 I _{D25} , pulse test	30	45	S	
C_{iss} C_{oss} C_{rss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz	3700		pF	
		860		pF	
		260		pF	
t_{d(on)} t_r t_{d(off)} t_f	V _{GS} = 10 V, V _{DS} = 0.5 V _{DSS} , I _D = 0.5 I _{D25} R _G = 2.0 Ω (External)	20		ns	
		18		ns	
		50		ns	
		14		ns	
Q_{g(on)} Q_{gs} Q_{gd}	V _{GS} = 10 V, V _{DS} = 0.5 V _{DSS} , I _D = 0.5 I _{D25}	105		nC	
		20		nC	
		44		nC	
R_{thJC}			0.31	K/W	
R_{thCK}	(TO-247)		0.25	K/W	

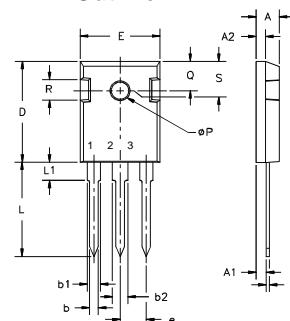
Symbol	Test Conditions	Characteristic Values			
		(T _J = 25°C, unless otherwise specified)	min.	typ.	max.
I_s	V _{GS} = 0 V			66	A
I_{SM}	Repetitive;			264	A
V_{SD}	I _F = I _S , V _{GS} = 0 V, Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %			1.5	V
t_{rr} Q_{RM} I_{RM}	I _F = 25A, -di/dt = 100 A/μs, V _R = 100 V		0.6	200	ns
			7		μC
					A

Min. Recommended Footprint

Dimensions in mm and inches



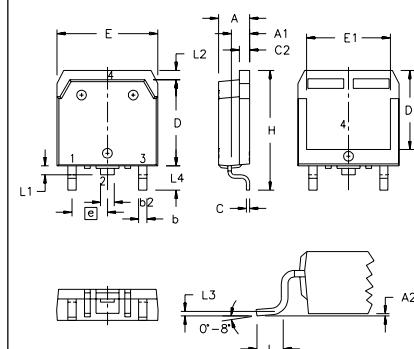
TO-247 AD Outline



Terminals: 1 - Gate
2 - Drain
3 - Source
Tab - Drain

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	.205	.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	.232	.252
R	4.32	5.49	.170	.216
S	6.15	BSC	242	BSC

TO-268 Outline



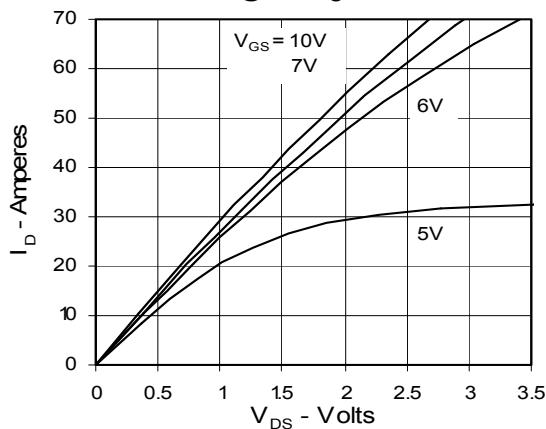
SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b2	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
e	.215 BSC		5.45 BSC	
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L1	.047	.055	1.20	1.40
L2	.039	.045	1.00	1.15
L3	.010 BSC		.025 BSC	
L4	.150	.161	3.80	4.10

IXYS reserves the right to change limits, test conditions, and dimensions.

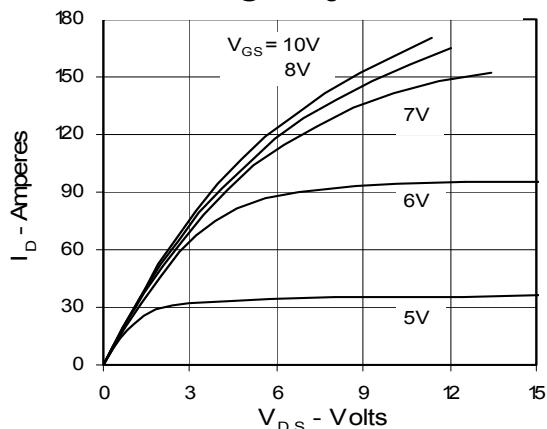
IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715 6,306,728B1 6,259,123B1 6,306,728B1
4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025 6,404,065B1 6,162,665 6,534,343

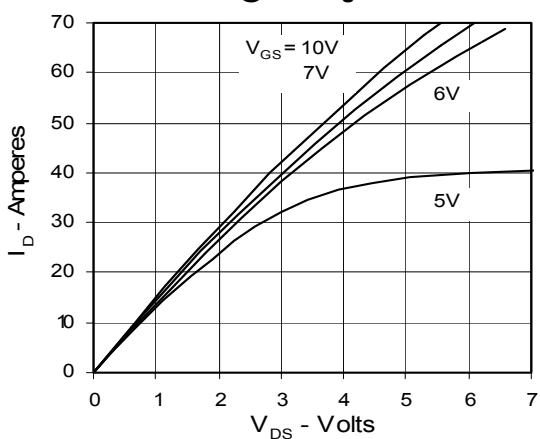
**Fig. 1. Output Characteristics
@ 25 Deg. C**



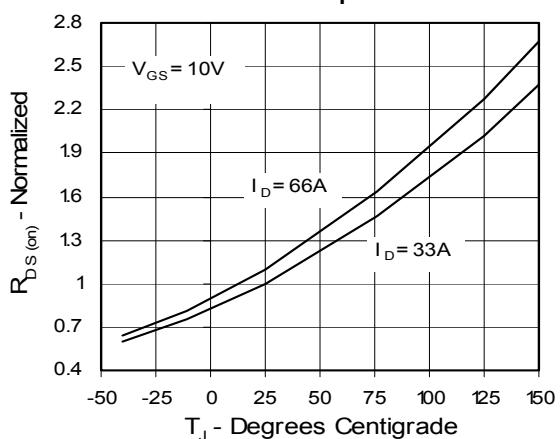
**Fig. 2. Extended Output Characteristics
@ 25 deg. C**



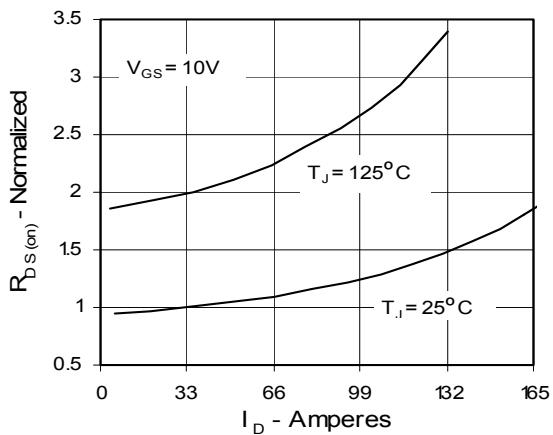
**Fig. 3. Output Characteristics
@ 125 Deg. C**



**Fig. 4. $R_{DS(on)}$ Normalized to I_{D25} Value vs.
Junction Temperature**



**Fig. 5. $R_{DS(on)}$ Normalized to I_{D25}
Value vs. I_D**



**Fig. 6. Drain Current vs. Case
Temperature**

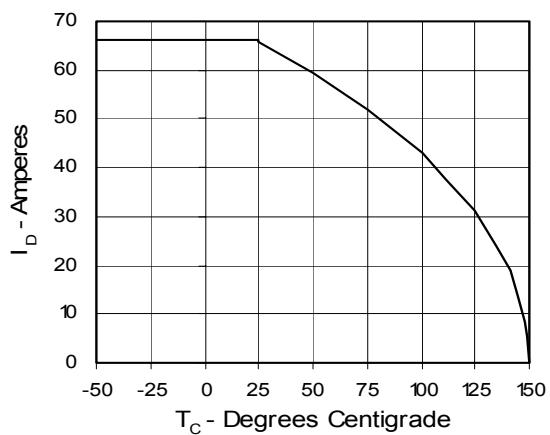
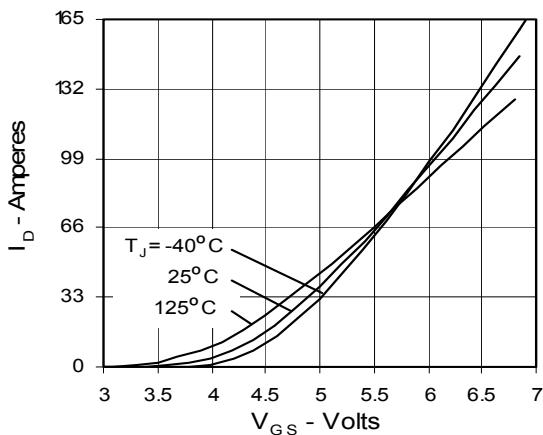
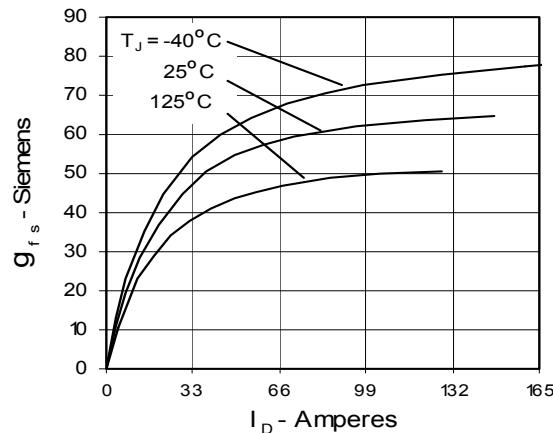
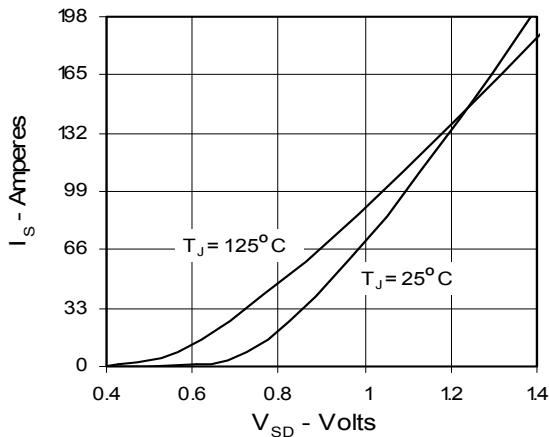
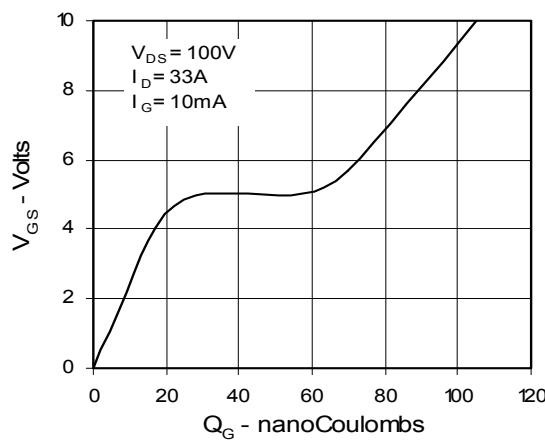
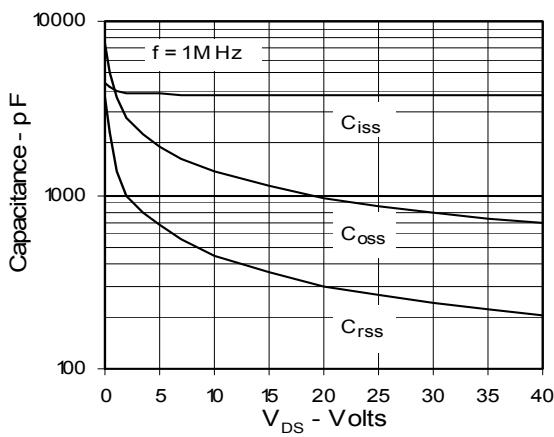
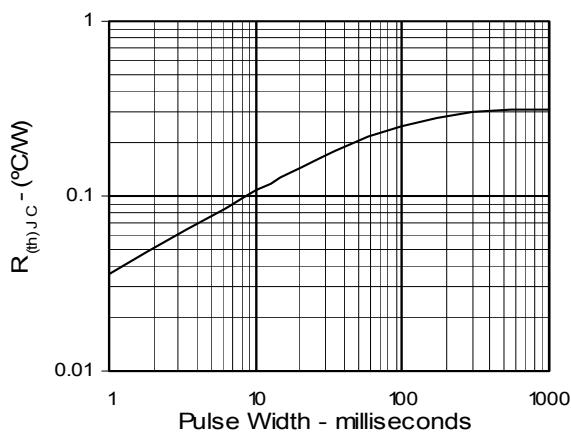


Fig. 7. Input Admittance

Fig. 8. Transconductance

Fig. 9. Source Current vs. Source-To-Drain Voltage

Fig. 10. Gate Charge

Fig. 11. Capacitance

Fig. 12. Maximum Transient Thermal Resistance


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